

METHOD AND APPARATUS FOR FABRICATING THIN FILM
TRANSISTOR INCLUDING CRYSTALLINE ACTIVE LAYER

5 ABSTRACT OF THE DISCLOSURE

The present invention relates to a method and apparatus for fabricating a thin film transistor including a crystalline silicon active layer. According to the method of the present invention, there are advantages in that processing time and production costs can be reduced since a series of processes of fabricating the thin film transistor, such as deposition of source metal, thermal annealing for crystallization, and deposition of an insulating layer or a wiring metal layer, can be consecutively performed in one apparatus.